

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-11. (Canceled)

12. (Currently amended) A production apparatus of a film, comprising:

means for heating a substrate comprising silicon,

plural dispersion heads for discharging independently gaseous compounds for forming the film,

means for positioning a bottom ~~discharge~~ end of a discharge port of a former dispersion head closer to a surface of the substrate than is a bottom ~~discharge~~ end of discharge port of a latter dispersion head,

means for conveying the silicon substrate, heated to a predetermined temperature, in a direction from a position immediately below ~~[[a]] the~~ discharge port of the former dispersion head to a position immediately below the discharge port ~~ports~~ of the latter dispersion ~~heads~~ head, and

a partition for surrounding a discharged gas ~~provided~~ between the latter dispersion head ~~heads~~ and the silicon substrate, the partition being positioned ~~[[at]]~~ below a circumference of bottom ends of the discharge port ~~dispersion ports~~ of the latter dispersion head.

13. (Canceled)

14. (Previously presented) The apparatus of claim 12, wherein said means for positioning and means for conveying cause a titanium oxide film to be formed in a non-uniform manner so that a concentration of the dopant element in the film varies through a thickness of the film so that the concentration of the dopant element in the titanium oxide film is higher adjacent a surface of the substrate than at a location spaced further away from the surface of the substrate.

15. (Previously presented) The apparatus of claim 12, wherein a difference between (i) a distance "A" from the bottom discharge end of the former dispersion head, and (ii) a distance "B" from the bottom discharge end of the latter dispersion head to the surface of the silicon substrate is from 0.1 to 30 mm.